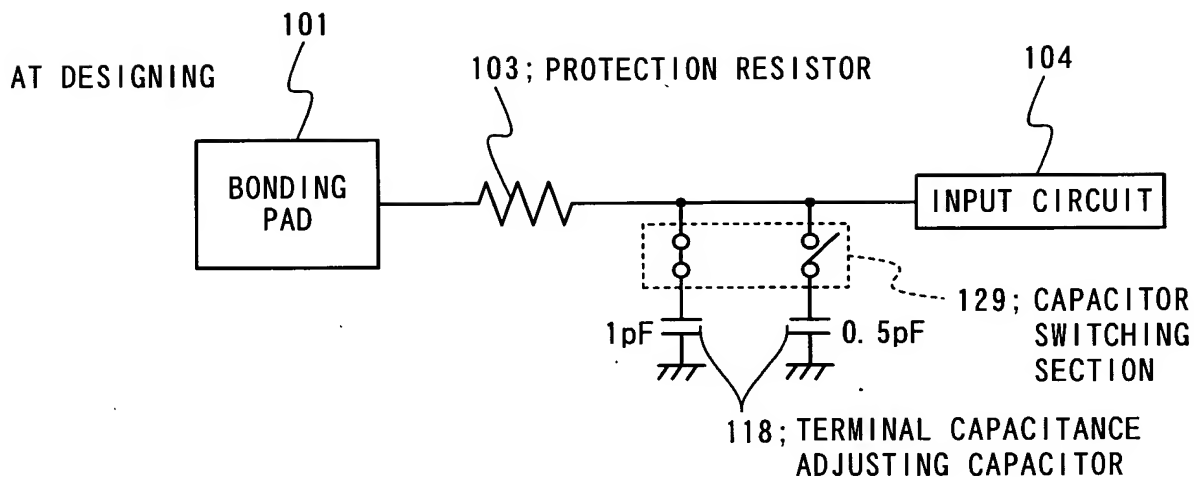


# Fig. 1 PRIOR ART

PACKAGE TYPE	TSOP	CSP	PRODUCT SPECIFICATIONS Max/Min
TERMINAL CAPACITANCE IN PACKAGE	1. 00	0. 14	3. 50/2. 50

# Fig. 2A PRIOR ART



# Fig. 2B PRIOR ART

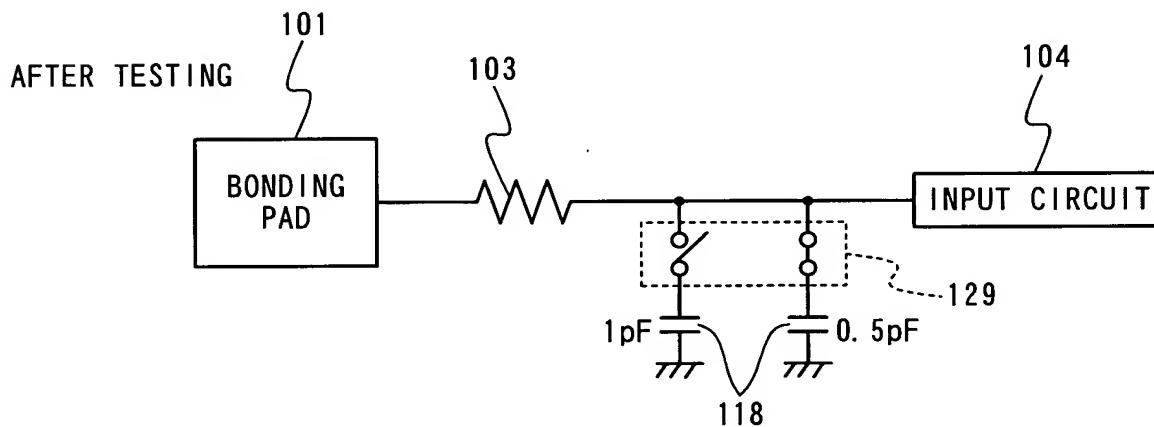
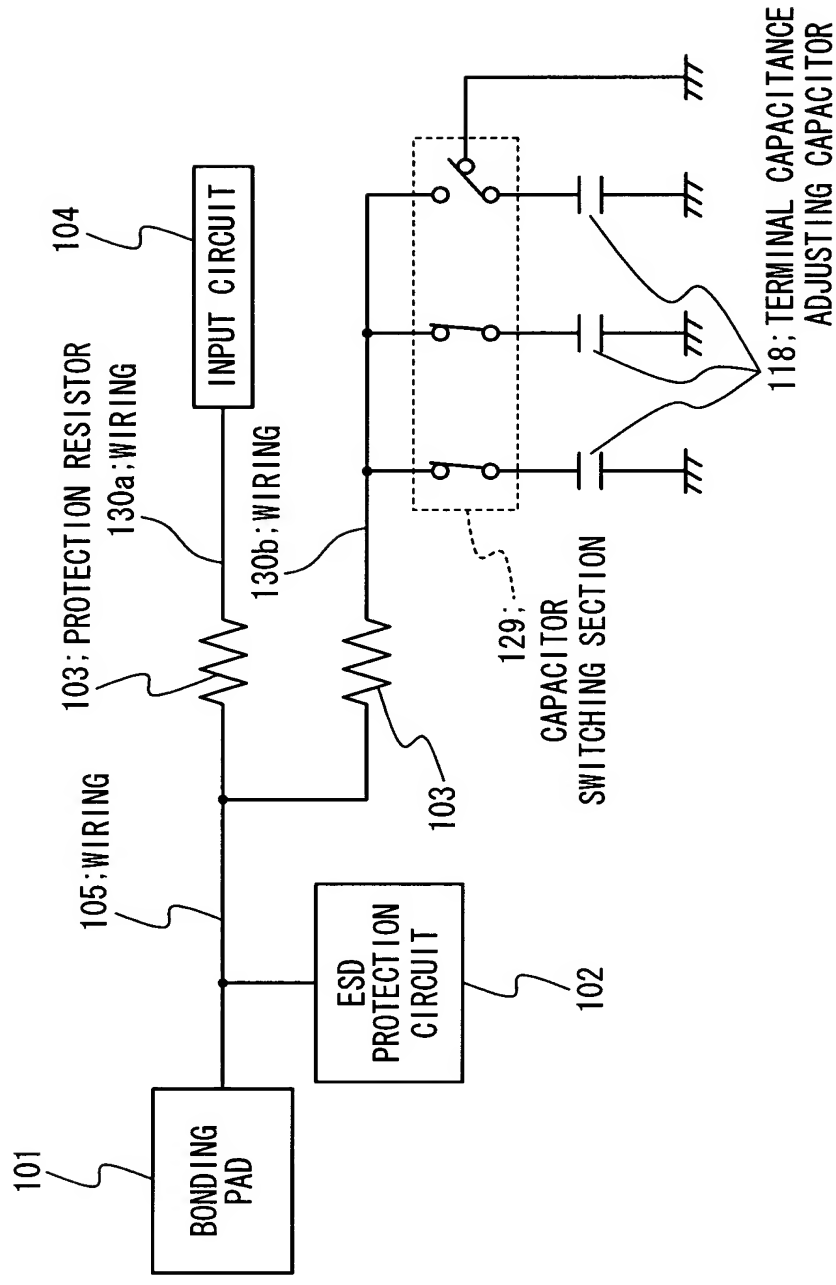
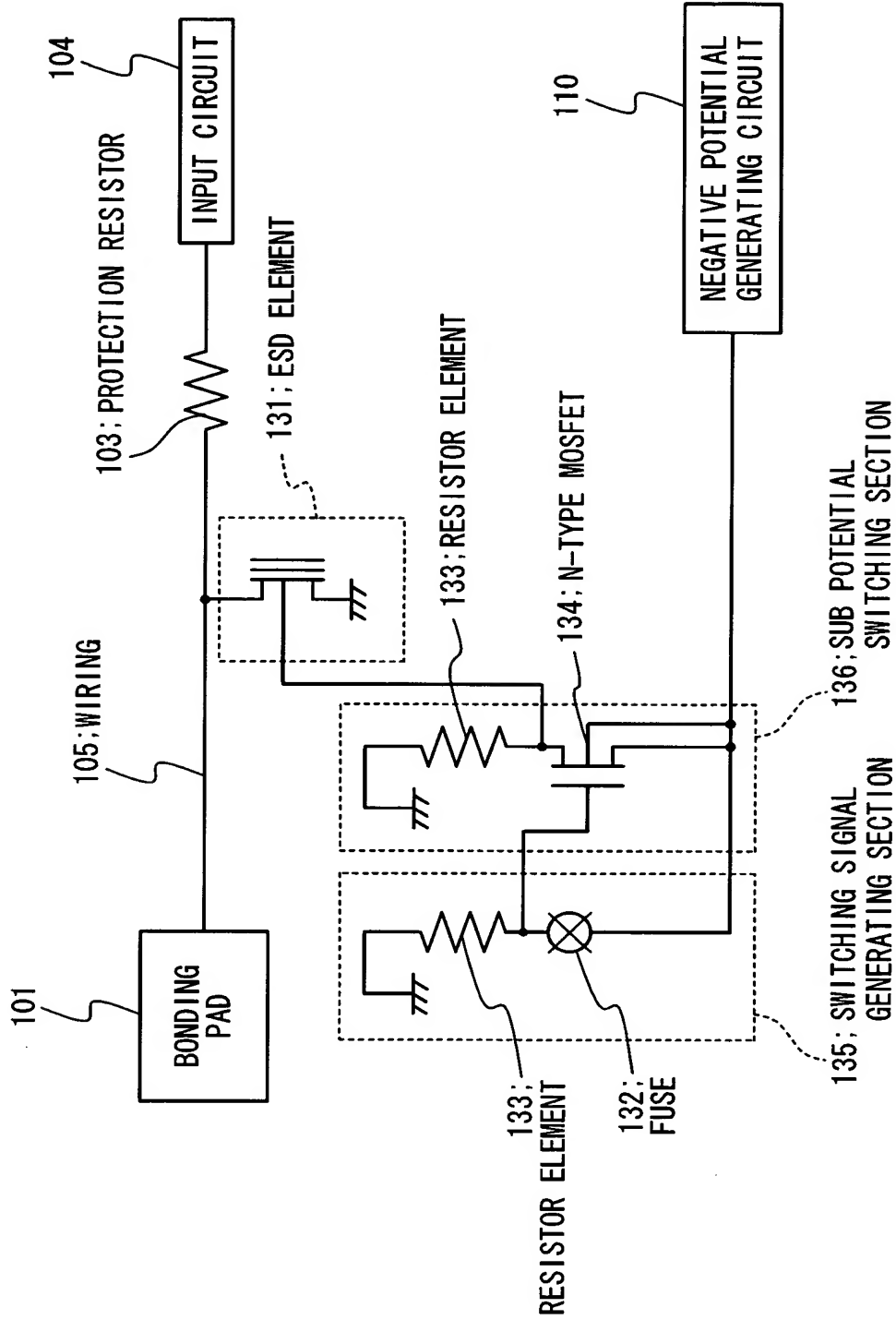


Fig. 3 PRIOR ART

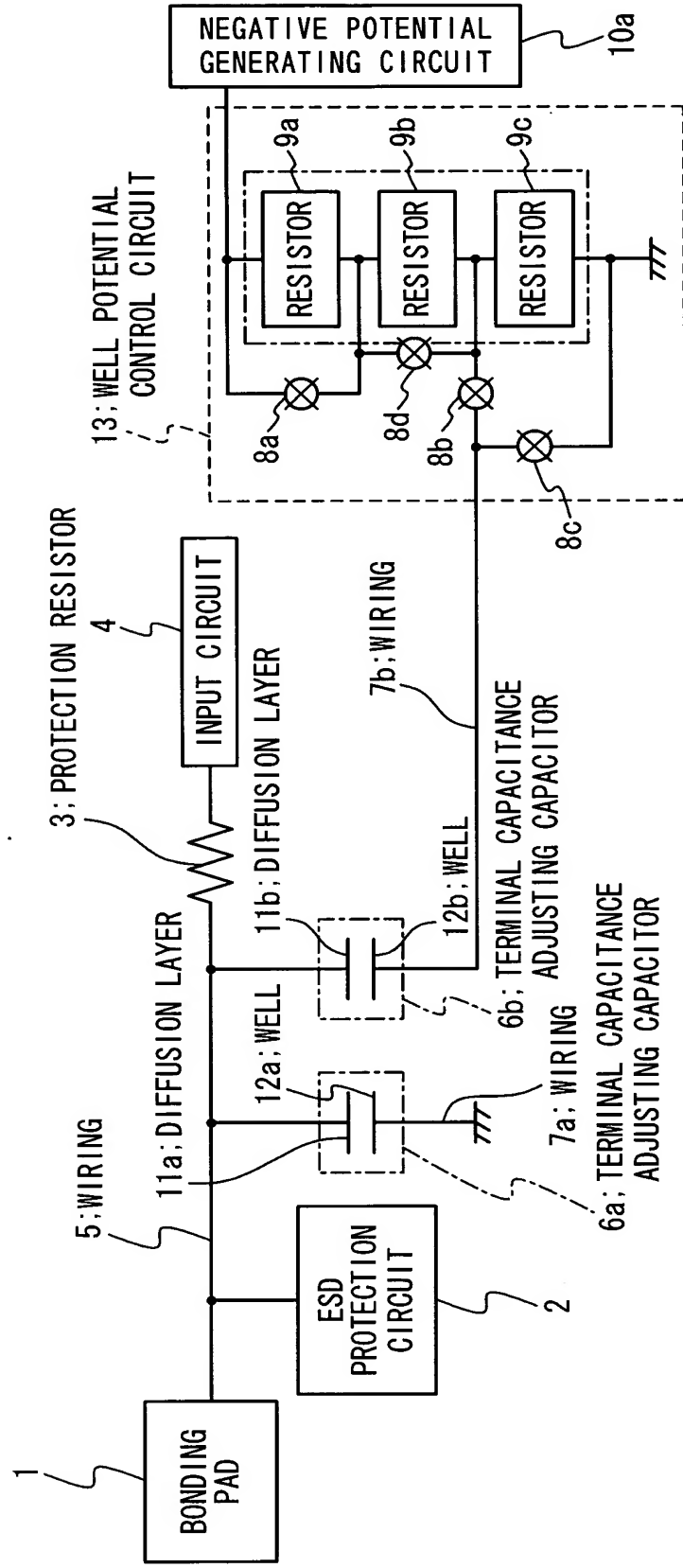


# Fig. 4 PRIOR ART

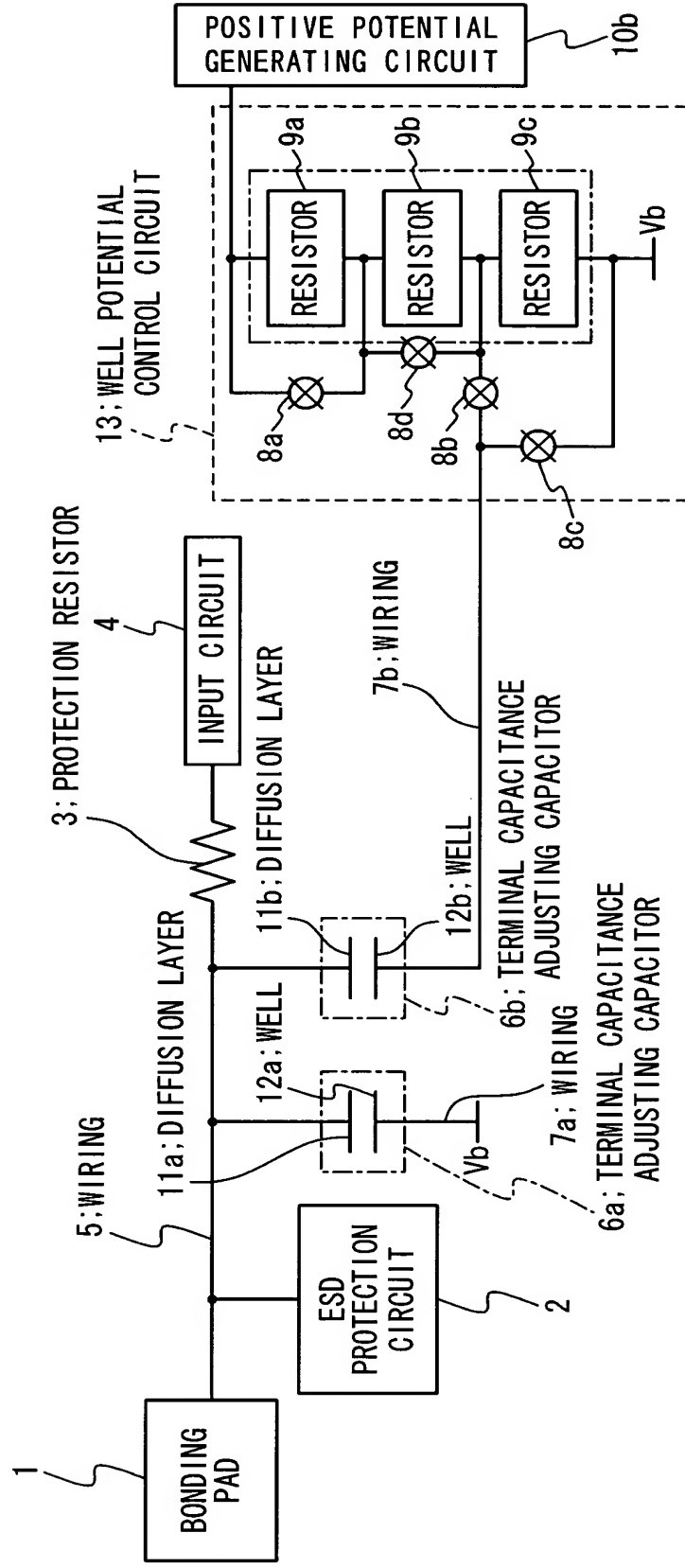


The schematic diagram of the semiconductor device 1 includes the following components and layers:

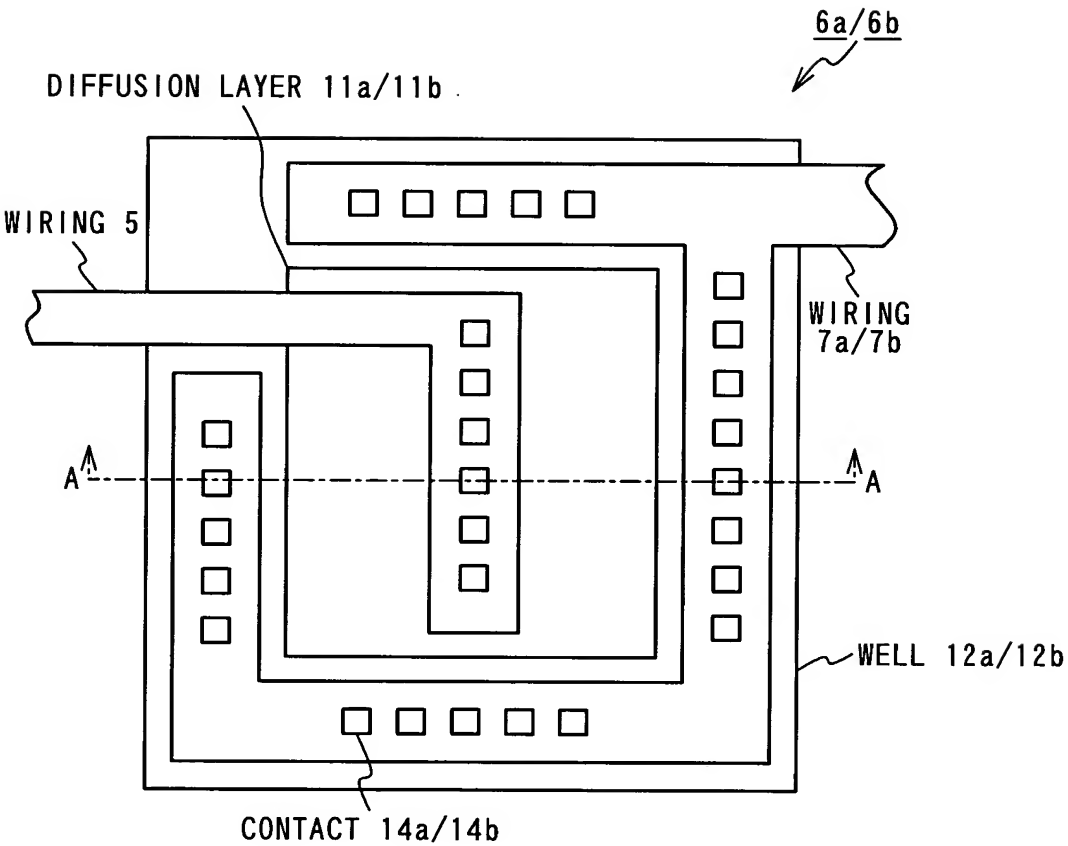
- 1: BONDING PAD** - Connected to the input circuit.
- 3: PROTECTION RESISTOR** - Connected between the bonding pad and the input circuit.
- 4: INPUT CIRCUIT** - Receives signals from the bonding pad.
- 5: WIRING** - Connects the input circuit to the diffusion layers.
- 11a: DIFFUSION LAYER** - Connected to the wiring and the ESD protection circuit.
- 11b: DIFFUSION LAYER** - Connected to the wiring and the terminal capacitance adjusting capacitors.
- 12a: WELL** - Underlies the first diffusion layer.
- 12b: WELL** - Underlies the second diffusion layer.
- 2: ESD PROTECTION CIRCUIT** - Connected to the first diffusion layer.
- 6a: TERMINAL CAPACITANCE ADJUSTING CAPACITOR** - Connected to the first diffusion layer.
- 6b: TERMINAL CAPACITANCE ADJUSTING CAPACITOR** - Connected to the second diffusion layer.
- 7a: WIRING** - Connected to the first terminal capacitance adjusting capacitor.
- 7b: WIRING** - Connected to the second terminal capacitance adjusting capacitor.
- 8a, 8b, 8c, 8d** - Switches or transistors controlling the capacitors.
- 9a, 9b, 9c** - Resistors in the well potential control circuit.
- 10a: NEGATIVE POTENTIAL GENERATING CIRCUIT** - Provides a negative potential to the well potential control circuit.
- 13: WELL POTENTIAL CONTROL CIRCUIT** - Controls the well potential using the resistors and switches.



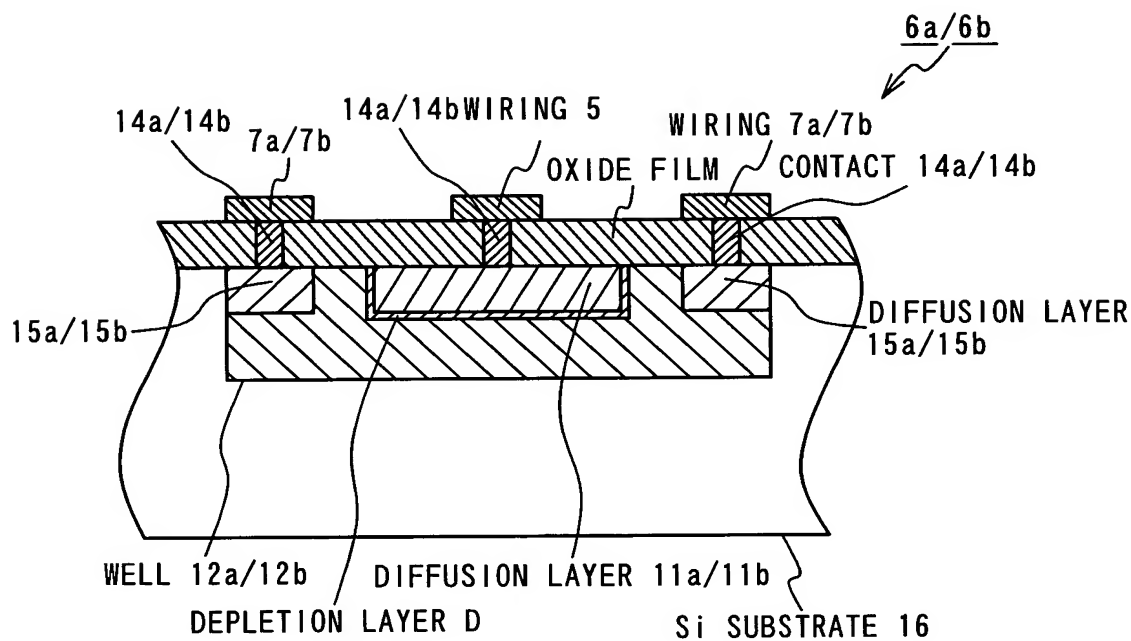
# Fig. 5B



**Fig. 6**



# Fig. 7



# Fig. 8

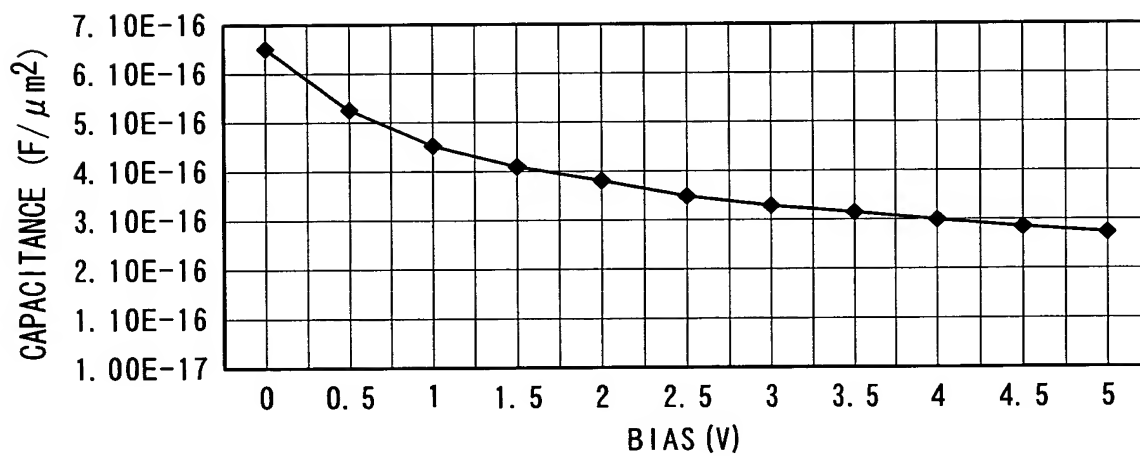




Fig. 9

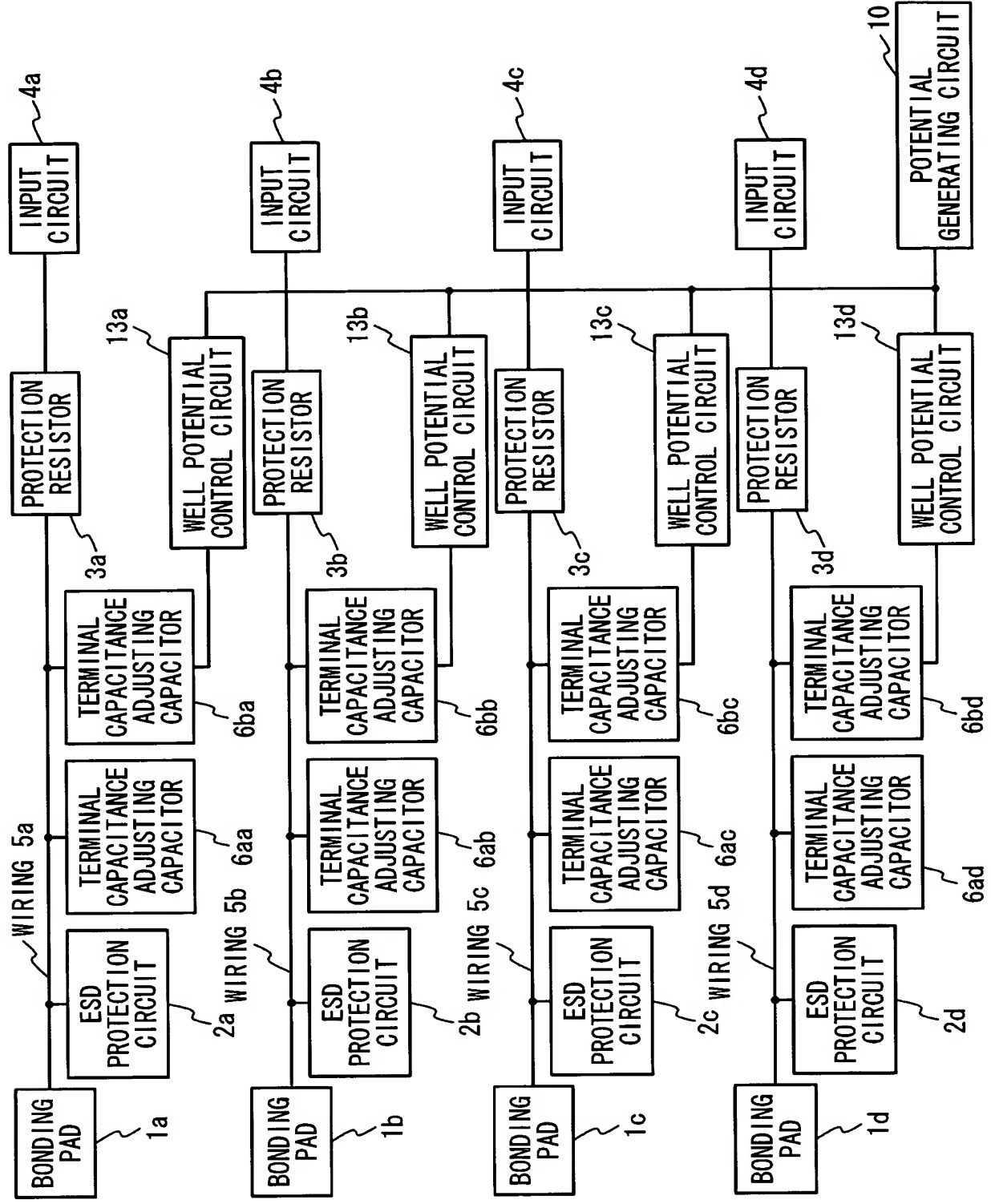


Fig. 10

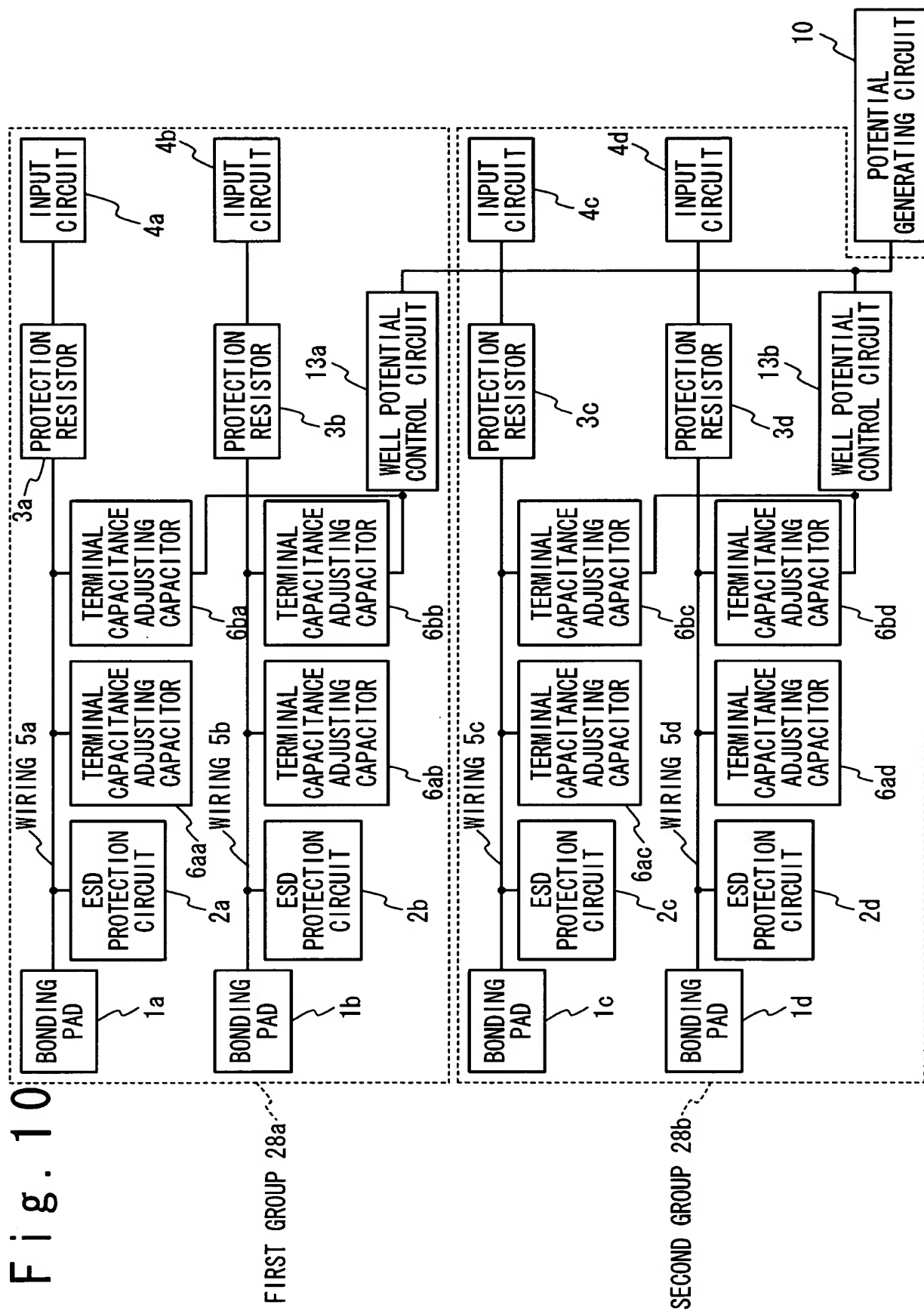
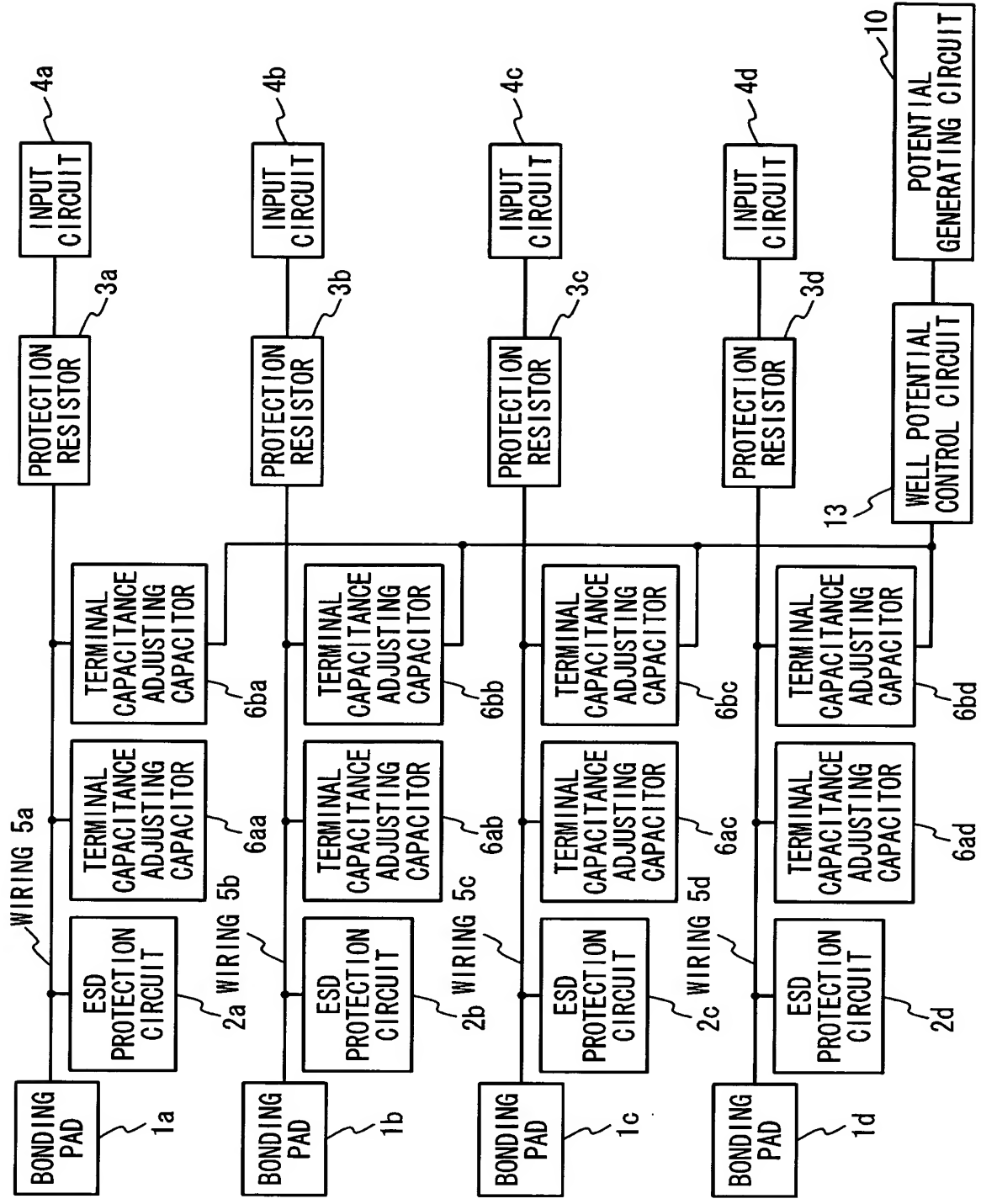
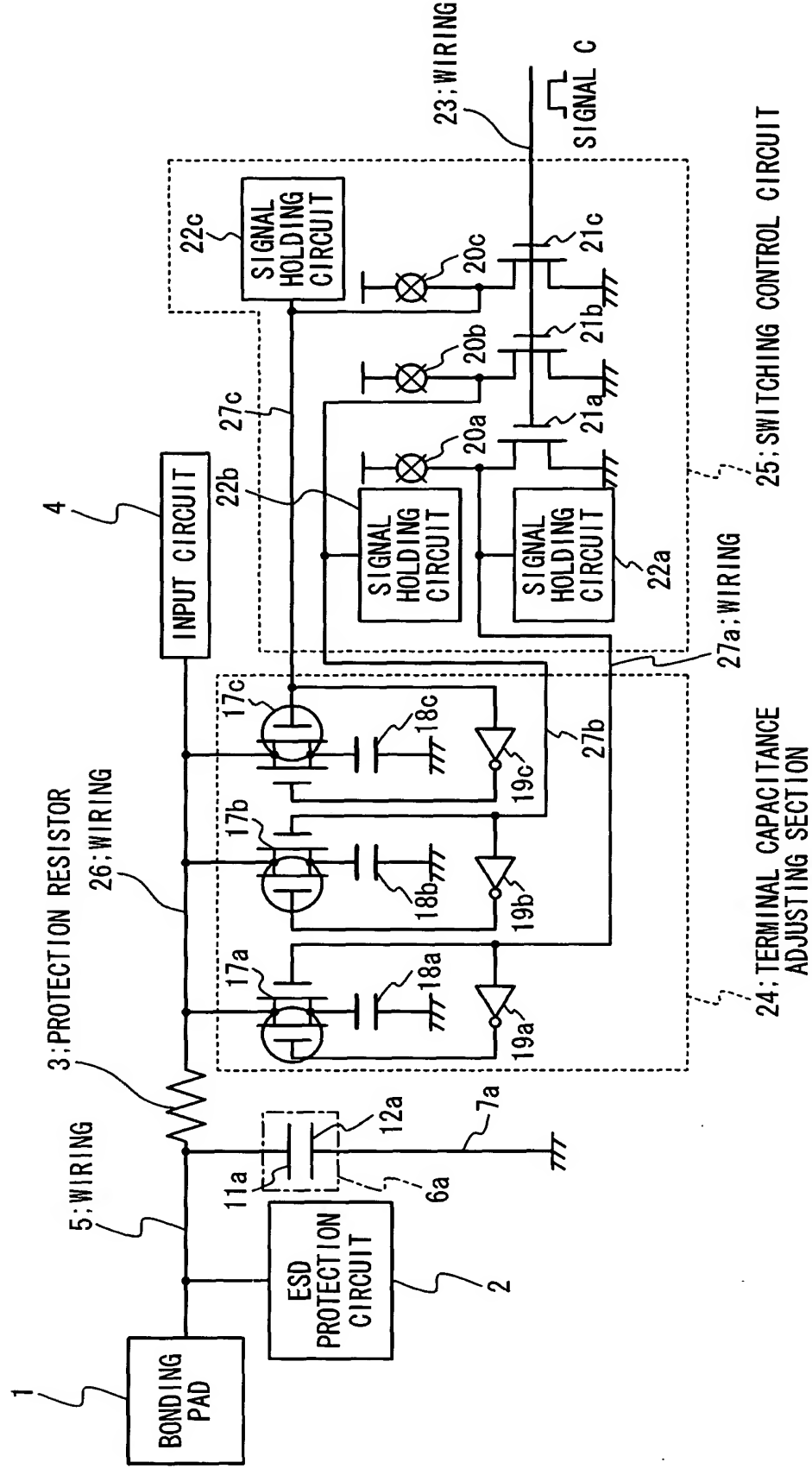


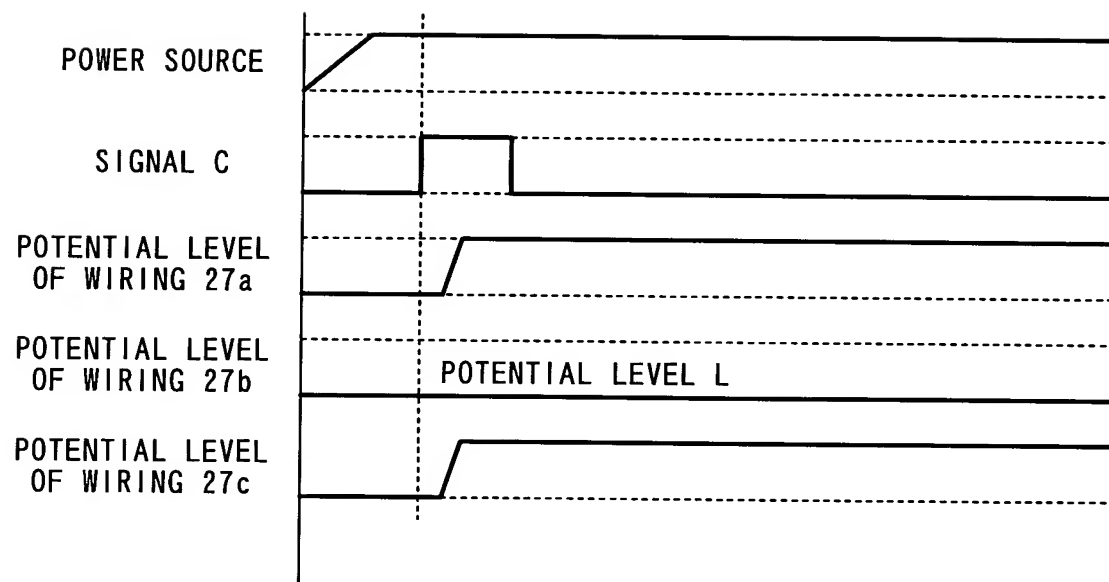
Fig. 11



# Fig. 12



F i g . 1 3



F i g . 1 4

	1	2	3	4	5	6	7	8
FUSE 20a	○	×	×	○	○	○	×	×
FUSE 20b	○	○	×	○	×	×	○	×
FUSE 20c	○	○	○	×	×	○	×	×
TOTAL TERMINAL CAPACITANCE	3pF	2pF	0pF	6pF	4pF	1pF	5pF	3pF

Fig. 15

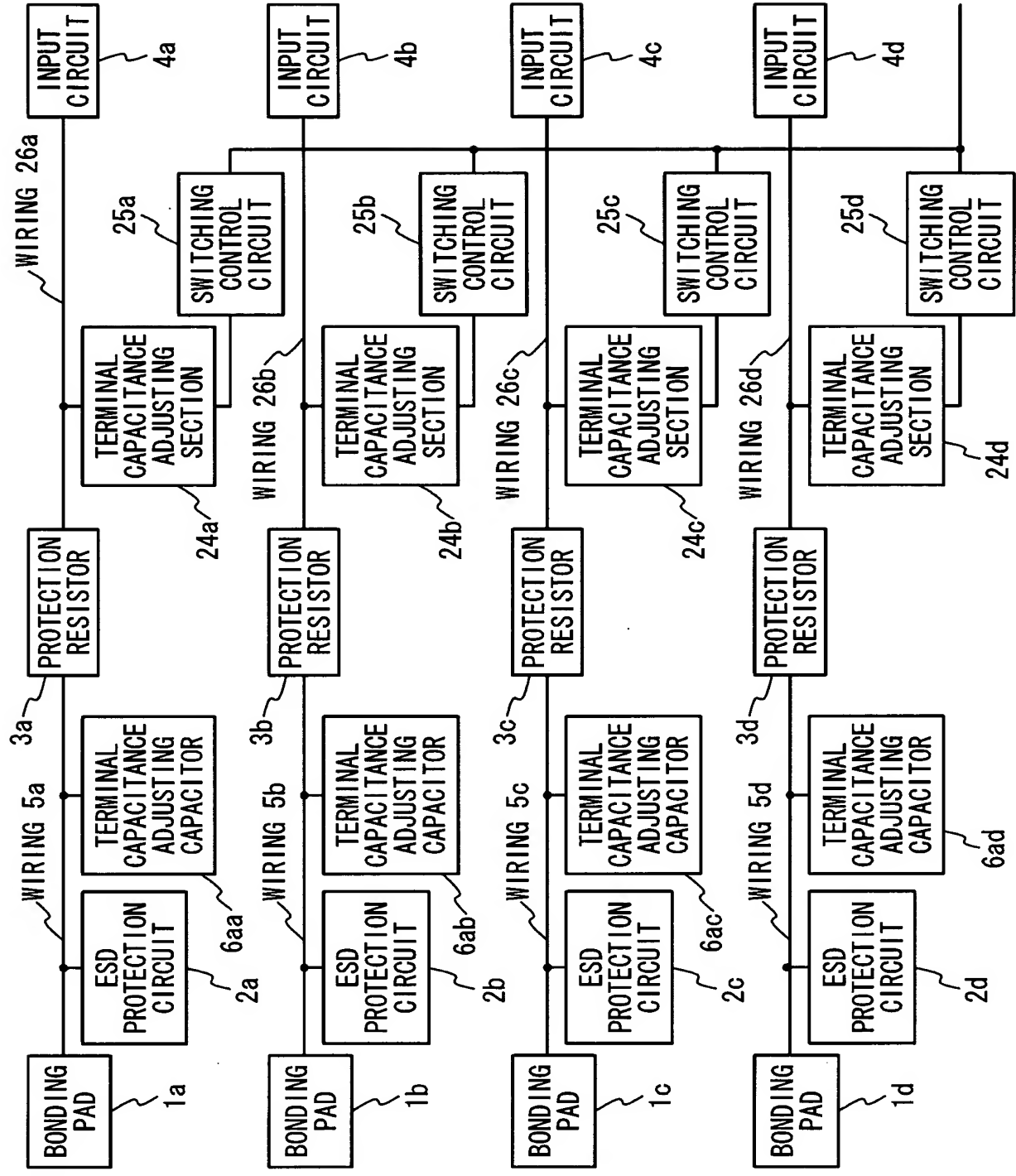


Fig. 16

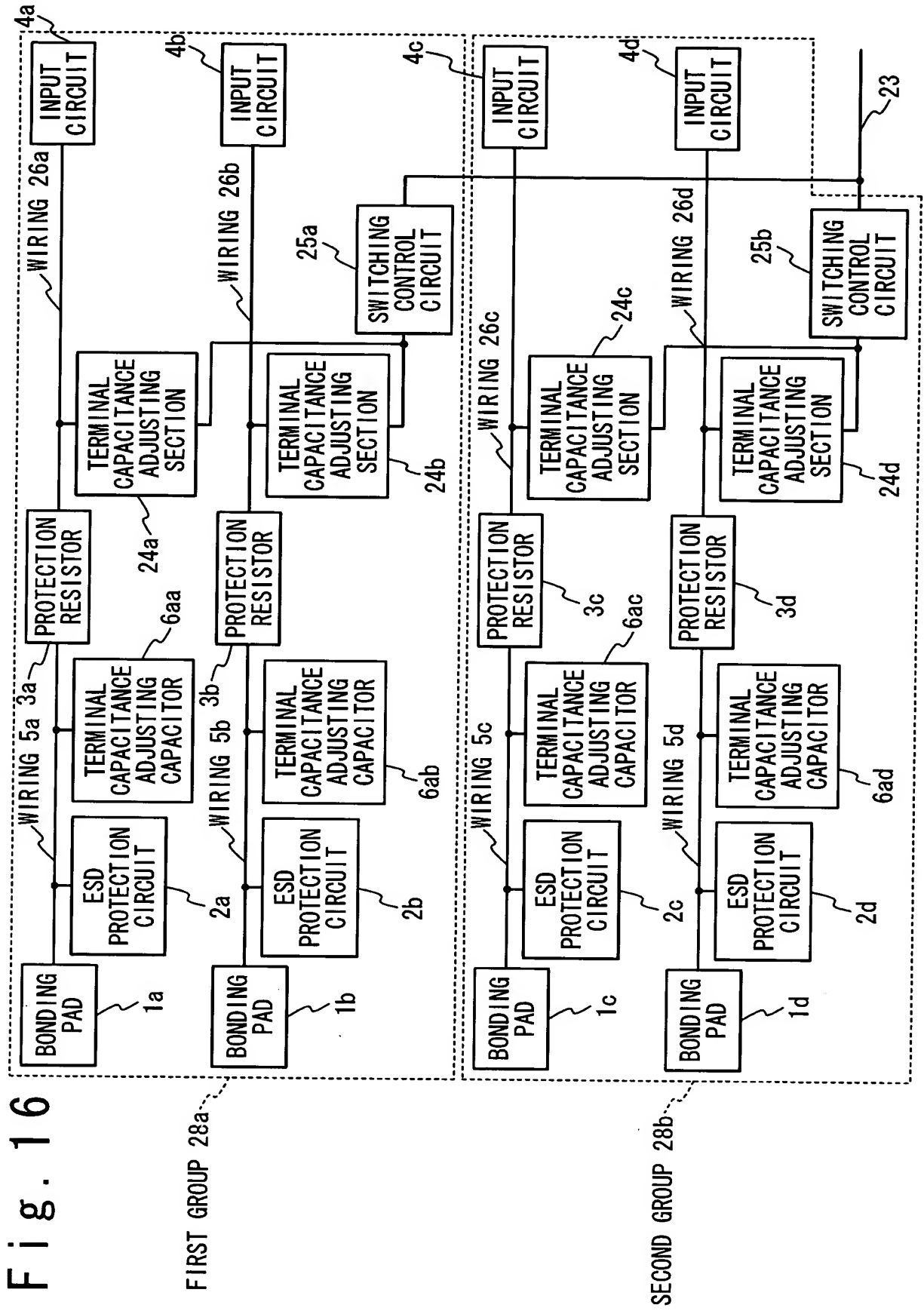




Fig. 17

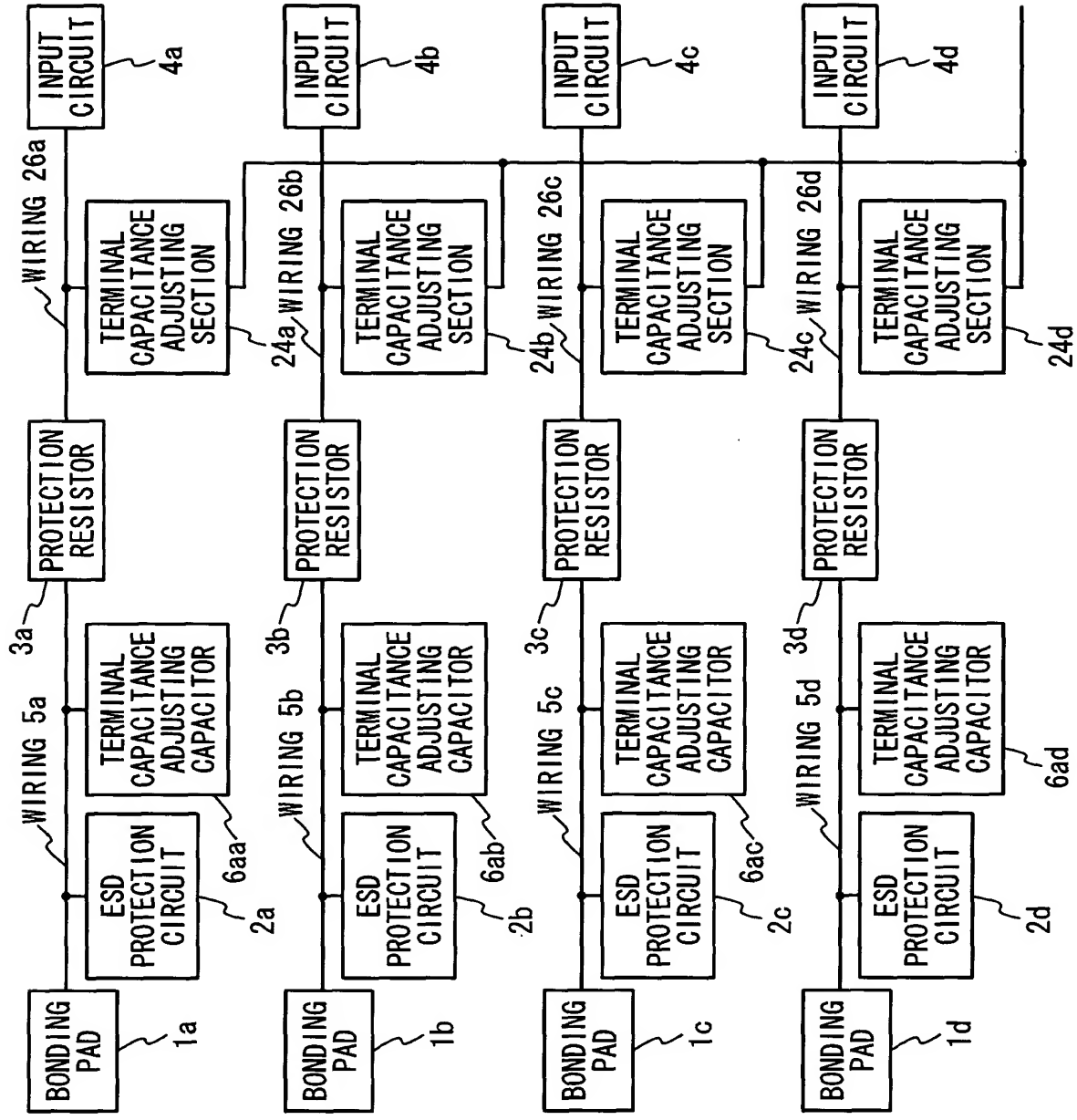
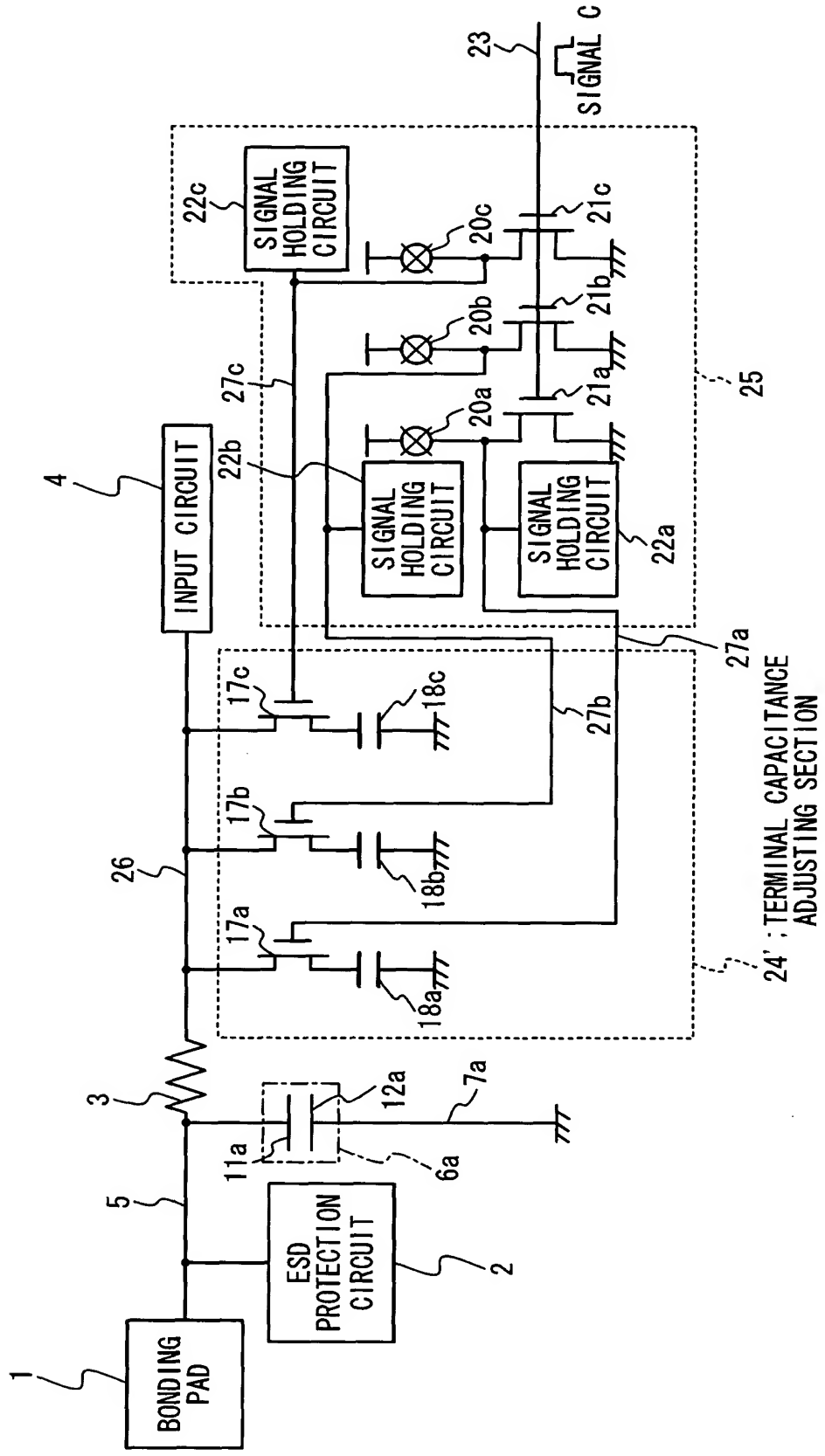
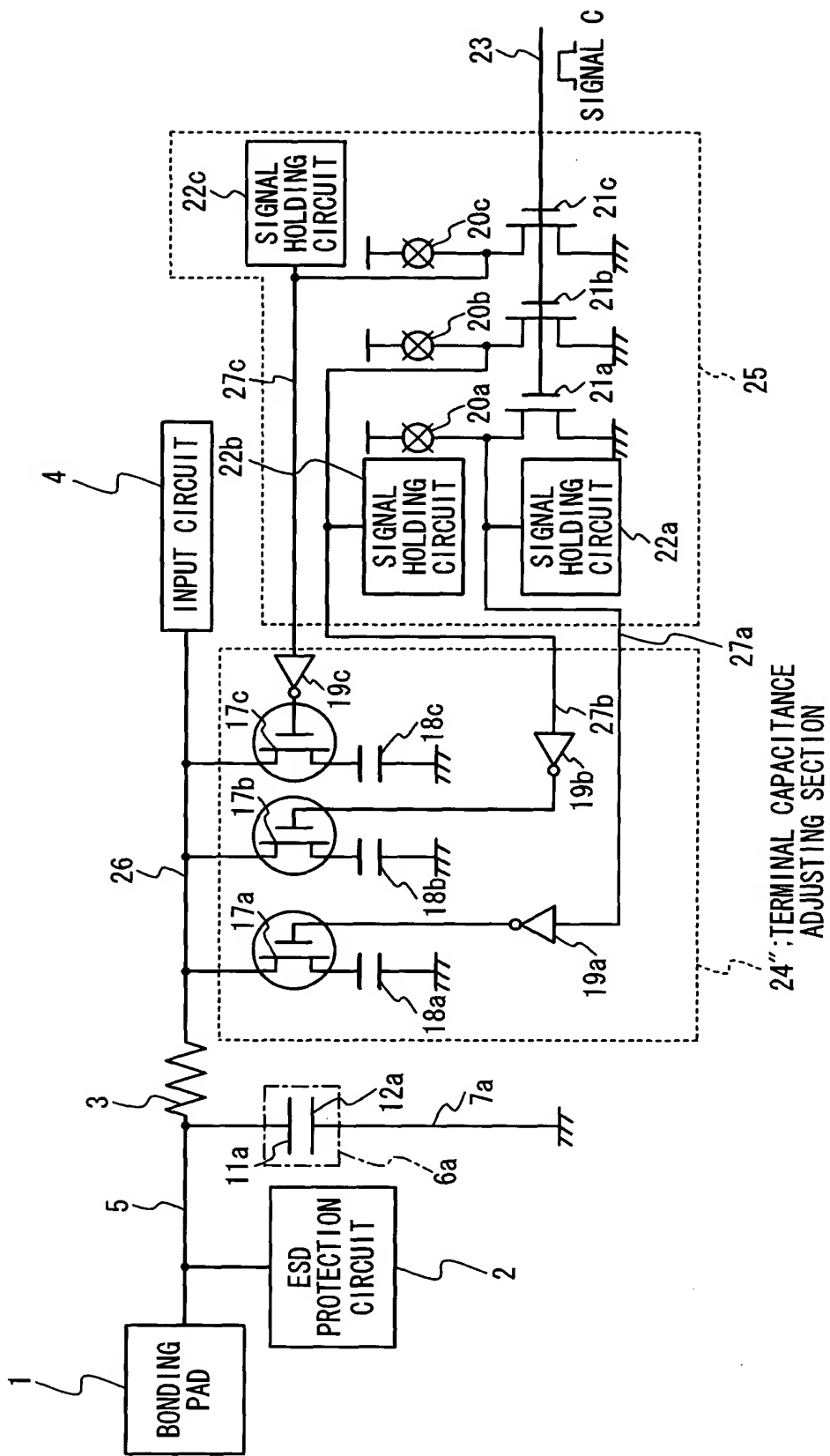


Fig. 18



The diagram illustrates a semiconductor device 1. It features a **BONDING PAD** (1) connected to an **ESD PROTECTION CIRCUIT** (2). The ESD protection circuit includes a MOSFET (11a) and a diode (12a). A resistor (3) is connected to the bonding pad. The input circuit (4) includes an **INPUT CIRCUIT** (22) and a **SIGNAL HOLDING CIRCUIT** (23). The terminal capacitance adjusting section (24) includes a **TERMINAL CAPACITANCE ADJUSTING SECTION** (24) and a **TERMINAL CAPACITANCE ADJUSTING SECTION** (25). The diagram shows various components like transistors, capacitors, and resistors, with labels 1 through 27c.



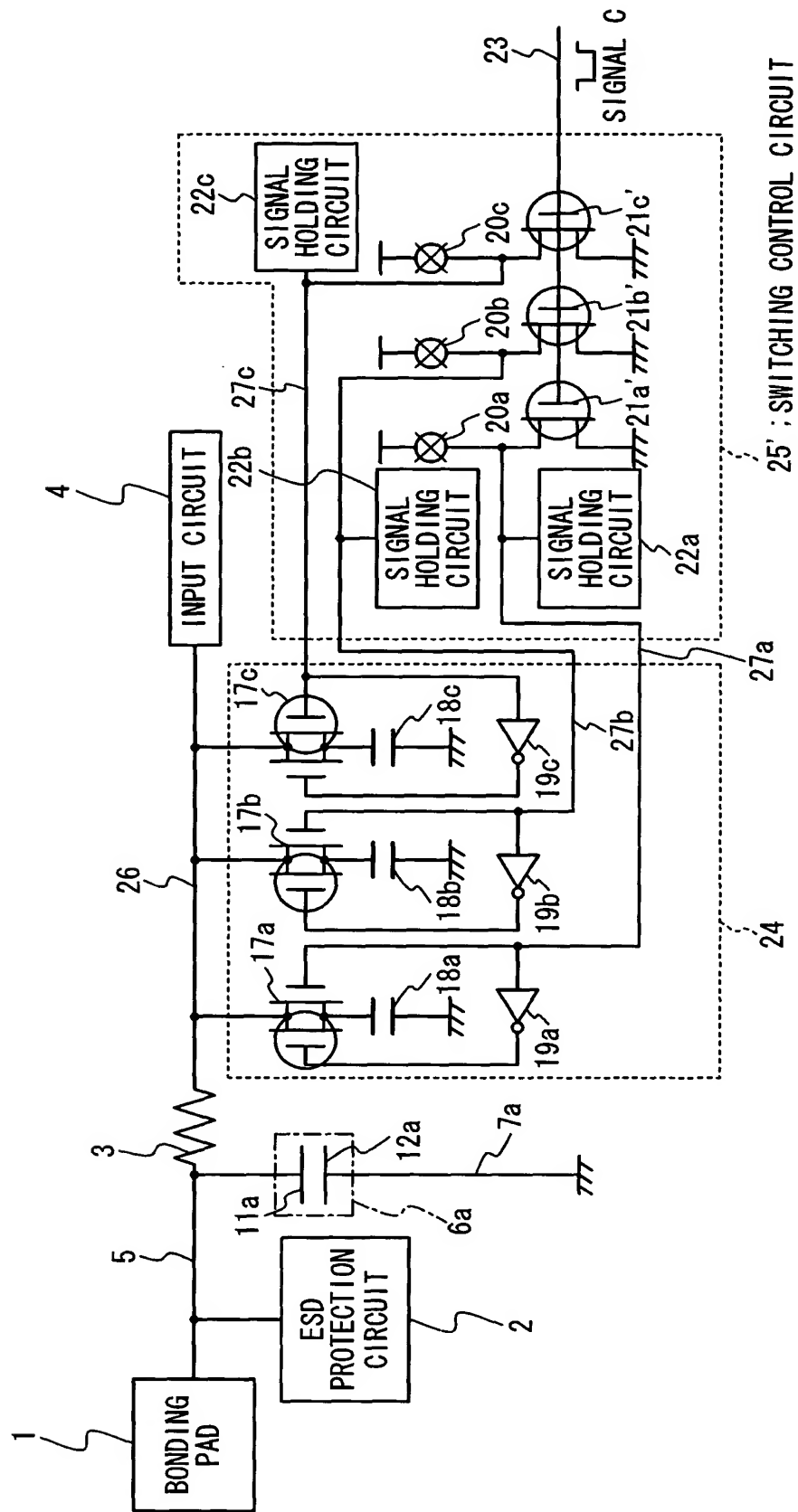
[illegible]

Fig. 21

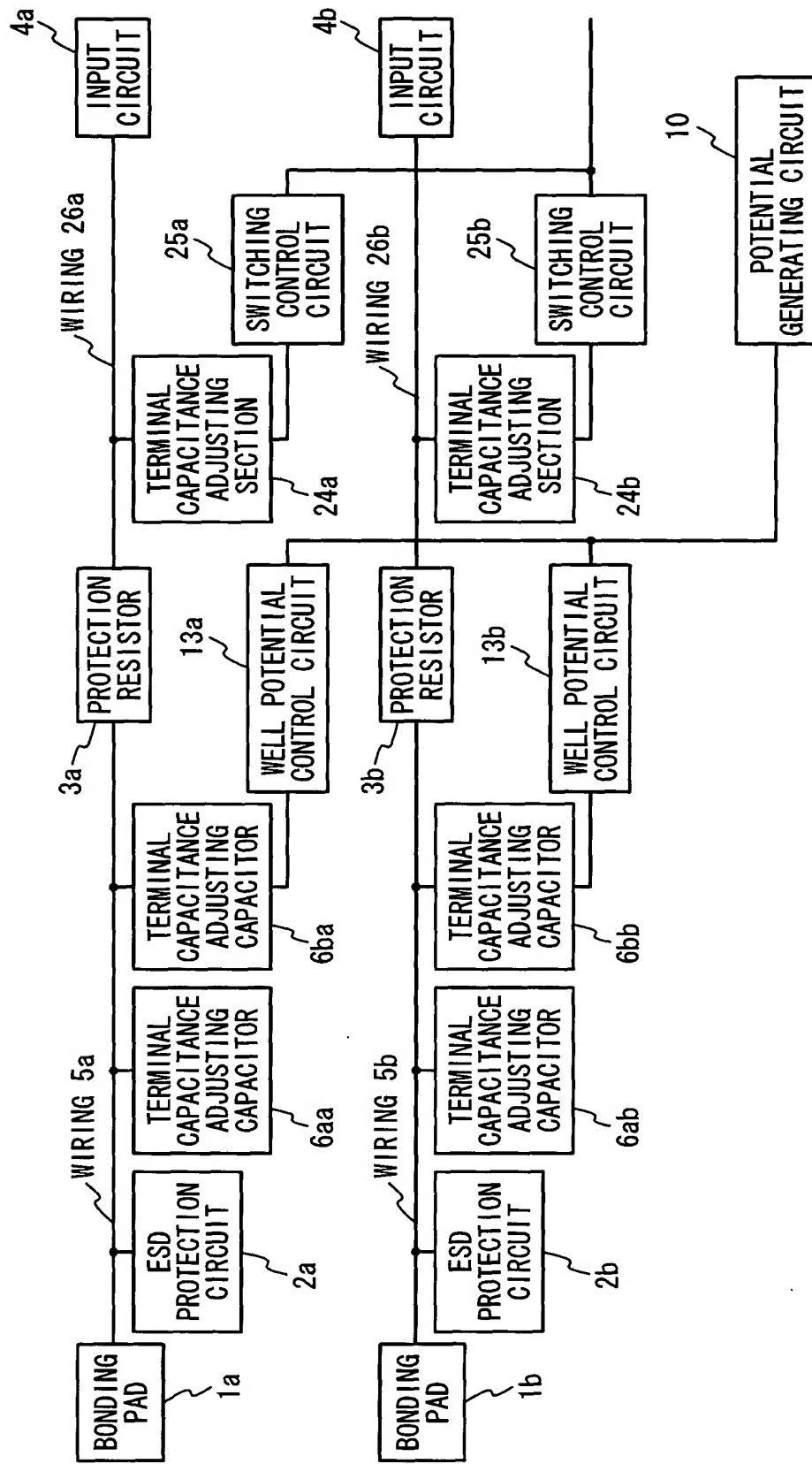


Fig. 22

